Application No.: 10/671,552 Docket No.: 8733.170.10-US

Amendment Dated July 9, 2004

Reply to Office Action dated April 9, 2004

Amendments to the Claims:

Claims 1-7 (Cancelled)

8. (New) A method of manufacturing a thin film transistor using a chemical vapor

deposition (CVD) apparatus having a frequency power supply, an electrode, and a gas inlet, the

method comprising:

placing a substrate on the electrode of the CVD apparatus; and

applying electric power having a frequency from the frequency power supply to the

electrode, while providing a reaction gas to the substrate via the gas inlet to form an insulator

layer on the substrate, the reaction gas having a mixture gas of monosilane and nitrous oxide.

9. (New) The method of claim 8, wherein the reaction gas includes a mixture gas of

monosilane and nitrous oxide having a flow ratio of between 10% and 50%.

10. (New) The method of claim 8, wherein a ratio of nitrous oxide to monosilane is at

least 10.

11. (New) The method of claim 8, wherein the reaction gas includes gas selected from

helium, hydrogen, xenon, oxygen, argon, nitrogen and a mixture thereof.

12. (New) The method of claim 8, wherein the insulator layer includes a gate insulator.

13. (New) The method of claim 8, wherein the insulator layer includes an interspacing

insulator.

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14. (New) The method of claim 8, wherein the insulator layer includes a silicon oxide layer.

15. (New) The method of claim 8, wherein the frequency is between 13.56 MHz and 100 MHz.

16. (New) The method of claim 8, wherein the frequency is about 40.68 MHz.

17. (New) The method of claim 8, wherein the frequency is about 27.12 MHZ.